

**In the Claims**

Claim 1-81 (cancelled).

Claim 82 (currently amended): A method of forming a low electrical resistance metal silicide, comprising:

forming a first metal silicide layer over a substrate, the first metal silicide layer having a melting point higher than 1700°C and being metal-enriched, the first metal silicide layer having a thickness of at least about 50Å and comprising a predominate metal;

forming depositing a metal-containing layer directly against the first metal silicide layer; the metal of the metal-containing layer predominately being a metal different than the predominant metal of the first metal silicide;

forming a silicon-containing layer directly against the metal-containing layer and on an opposing side of the metal-containing layer from the first metal silicide layer;

after forming the silicon-containing layer, converting the metal of the metal-containing layer to metal silicide to convert the metal-containing layer to a second metal silicide layer over the substrate; the second metal silicide layer having a bulk resistance of less than 30 micro-ohms-centimeter; the conversion of the metal of the metal-containing layer to the second metal silicide layer comprising incorporation of silicon from the silicon-containing layer into the second metal silicide layer; and

patterning the first metal silicide layer, second metal silicide layer and silicon-containing layer into a line having substantially vertical sidewalls extending along the first metal silicide layer, second metal silicide layer and silicon-containing layer.

Claim 83 (previously presented): The method of claim 82 wherein the first metal silicide layer is formed on a non-silicon-containing electrically conductive material.

Claim 84 (previously presented): The method of claim 82 wherein the silicon-containing layer consists essentially of silicon or conductively-doped silicon.

Claim 85 (previously presented): The method of claim 82 further comprising forming a layer comprising silicon nitride over the silicon-containing layer, and wherein the patterning also patterns the layer comprising silicon nitride into the line.

Claim 86 (previously presented): The method of claim 82 wherein the substrate comprises silicon, and wherein the first metal silicide layer is formed directly against the silicon of the substrate.

Claim 87 (previously presented): The method of claim 82 wherein the first metal silicide layer consists essentially of tantalum silicide, and wherein the second metal silicide layer consists essentially of titanium silicide.

Claims 88-97 (canceled).